

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-61 (Cancelled).

Claim 62 (New): A correction method for correction of an erroneous design made in a first thin layer including at least one first engraved sub-layer including the erroneous design and at least one second sub-layer located between a substrate and the first sub-layer, the method comprising:

- a) depositing a second thin layer on the first thin layer;
- b) lithography of the second thin layer, as a function of a desired correction or corrections,
  - etching the first sub-layer through the second thin layer;
  - removing the second thin layer;
  - depositing a third thin layer on the first sub-layer; and
  - second lithography in the third thin layer leaving blocks filling the patterns in excess;
- and
- c) etching the second sub-layer through the first sub-layer.

Claim 63 (New): A correction method as claimed in claim 62, the lithography being carried out by one or more optical particle beams.

Claim 64 (New): A method as claimed in claim 63, the one or more optical particle beams being selected from among: an ion beam, an electron beam, a proton beam, an X-ray beam, a laser beam, an UV beam.

Claim 65 (New): A method as claimed in claim 64, the beam being controlled by a digital device associated with a data medium including data relative to the erroneous design and to a desired corrected design.

Claim 66 (New): A lithography device carrying out one or more of the lithography of the method as claimed in claim 62, comprising:

first means for producing at least one lithography beam;

second means for processing data relative to an erroneous design formed in a thin layer, and data relative to a desired corrected design, and for producing correction data following such processing; and

third means for controlling the first means, from correction data produced by the second means.

Claim 67 (New): A correction method for correction of an erroneous design made in a first thin layer including at least one first engraved sub-layer including the erroneous design and at least one second sub-layer located between a substrate and the first sub-layer, the method comprising:

a) depositing a second thin layer on the first thin layer;

b) lithography of the second thin layer, as a function of a desired correction or corrections, etching the first sub-layer through the second thin layer;

removing the second thin layer after the etching of the first sub-layer through the second thin layer; and

c) etching the second sub-layer through the first sub-layer.

Claim 68 (New): A method as claimed in claim 67, the second thin layer being a resin or polymer layer.

Claim 69 (New): A method as claimed in claim 67, the lithography being carried out by one or more optical particle beams.

Claim 70 (New): A method as claimed in claim 69, the one or more optical particle beams being selected from among: an ion beam, an electron beam, a proton beam, an X-ray beam, a laser beam, an UV beam.

Claim 71 (New): A method as claimed in claim 70, the beam being controlled by a digital device associated with a data medium including data relative to the erroneous design and to a desired corrected design.

Claim 72 (New): A lithography device carrying out one or more of the lithography of the method as claimed in claim 67, comprising:

first means for producing at least one lithography beam;

second means for processing data relative to an erroneous design formed in a thin layer, and data relative to a desired corrected design, and for producing correction data following such processing; and

third means for controlling the first means, from correction data produced by the second means.

Claim 73 (New): A correction method for correction of an erroneous design made in a first thin layer including at least one first engraved sub-layer including the erroneous design and at least one second sub-layer located between a substrate and the first sub-layer, the method comprising:

a) depositing a second thin layer covering said first thin layer;

b) lithography of the second thin layer, as a function of desired corrections; and

c) etching the second sub-layer through the first sub-layer;

the method further comprising after step c):

removing said first sub-layer.

Claim 74 (New): A method as claimed in claim 73, the lithography being carried out by direct writing.

Claim 75 (New): A method as claimed in claim 73, the lithography being carried out by one or more optical particle beams.

Claim 76 (New): A method as claimed in claim 75, the one or more optical particle beams being selected from among: an ion beam, an electron beam, a proton beam, an X-ray beam, a laser beam, an UV beam.

Claim 77 (New): A method as claimed in claim 76, the beam being controlled by a digital device associated with a data medium including data relative to the erroneous design and to a desired corrected design.

Claim 78 (New): A lithography device carrying out one or more of the lithography of the method as claimed in claim 73, comprising:

first means for producing at least one lithography beam;

second means for processing data relative to an erroneous design formed in a thin layer, and data relative to a desired corrected design, and for producing correction data following such processing; and

third means for controlling the first means, from correction data produced by the second means.